MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet









SMB

Features

- For surface mounted application
- Glass passivated junction chip
- Built-in strain relief, ideal for automated placement
- Plastic material used carries Underwriters Laboratory Classification 94V-O
- Fast switching for high efficiency
- High temperature soldering: 260°C /10 seconds at terminals

Mechanical Data

Cases: Molded plastic Terminals: Solder plated

Polarity: Indicated by cathode band Packing: 16mm tape per E1A STD

> RS-481 Weight: 0.09 gram

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%

Type Number	Symbol	RS 3A	RS 3B	RS 3D	RS 3G	RS 3J	RS 3K	RS 3M	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current See Fig. 1 @T _L =75°C	I _(AV)	3.0				Α			
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	100				Α			
Maximum Instantaneous Forward Voltage @ 3.0A	V _F	1.3			V				
Maximum DC Reverse Current @ T _A =25°C at Rated DC Blocking Voltage @ T _A =125°C	I _R	10 250				uA uA			
Maximum Reverse Recovery Time (Note 1)	Trr	150 2		250 500		nS			
Typical Junction Capacitance (Note 2)	Cj	60			pF				
Typical Thermal Resistance (Note 3)	$R heta_{JA}$	50.0 15.0			°C\W C\W				
	$R\theta_{JL}$								
Operating Temperature Range	TJ	-55 to +150			℃				
Storage Temperature Range	T_{STG}	-55 to +150			${f c}$				

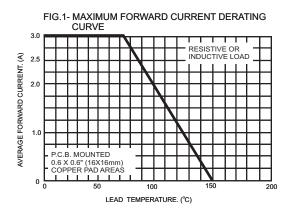
Notes: 1. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

- 2. Measured at 1 MHz and Applied VR=4.0 Volts
- 3. Thermal Resistance from Junction to Ambient and from Junction to Lead Mounted on P.C.B. with 0.6"x0.6" (16 x 16 mm) Copper Pad Areas.









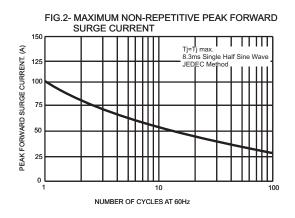


FIG.3- TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

100

Tj=125°C

Tj=25°C

Pulse Width=300µs
1% Duty Cycle

1 Tj=-40°C

FORWARD VOLTAGE. (V)

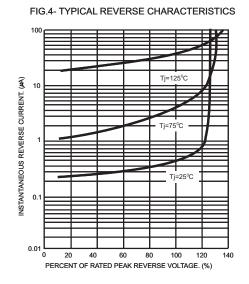
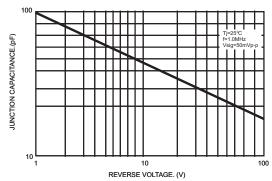


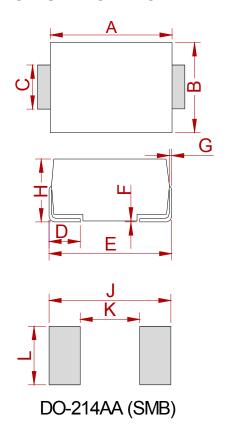
FIG.5- TYPICAL JUNCTION CAPACITANCE





Semiconductor Compia

PACKAGE MECHANICAL DATA



	Dimensions					
Ref. Millimeters		neters	Inches			
	Min.	Max.	Min.	Max.		
Α	4.25	4.75	0.167	0.187		
В	3.30	3.94	0.130	0.155		
С	1.85	2.21	0.073	0.087		
D	0.76	1.52	0.030	0.060		
Е	5.08	5.59	0.200	0.220		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	2.11	2.44	0.083	0.096		
J	6.80		0.270			
K		2.60		0.100		
L	2.40		0.090			

REEL SPECIFICATION

P/N	PKG	QTY
RS3A THRU RS3M	SMB	3000



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